



ACTT8B-800CTN

Enhanced and high temperature ACTT power switch

14 May 2015

Product data sheet

1. General description

AC Thyristor Triac power switch in a SOT404 (D2PAK) surface mountable plastic package with self-protective clamping capabilities against low and high energy transients. This "series CTN" triac will commute the full RMS current at the maximum rated junction temperature ($T_{j(max)} = 150\text{ }^{\circ}\text{C}$) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- High junction operating temperature capability ($T_{j(max)} = 150\text{ }^{\circ}\text{C}$)
- High minimum I_{GT} for guaranteed immunity to gate noise
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Less sensitive gate for high noise immunity
- Surface mountable package
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt and IEC 61000-4-4 fast transient
- Package meets UL94V0 flammability requirement
- Package is RoHS compliant

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls
- Applications subject to high temperature ($T_{j(max)} = 150\text{ }^{\circ}\text{C}$)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V

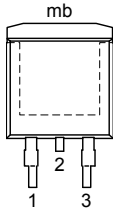
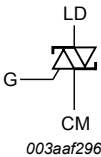


Enhanced and high temperature ACTT power switch

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	80	A
T_j	junction temperature		-	-	150	$^{\circ}\text{C}$
$I_{T(\text{RMS})}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 131\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	8	A
V_{PP}	peak pulse voltage	$T_j = 25\text{ }^{\circ}\text{C}$; non-repetitive, off-state; Fig. 6	-	-	2	kV
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 100\text{ mA}$; LD+ G+; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 8	5	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 100\text{ mA}$; LD+ G-; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 8	5	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 100\text{ mA}$; LD- G-; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 8	5	-	35	mA
V_{CL}	clamping voltage	$I_{CL} = 0.1\text{ mA}$; $t_p = 1\text{ ms}$; $T_j = 25\text{ }^{\circ}\text{C}$	850	-	-	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 125\text{ }^{\circ}\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	4000	-	-	V/ μs
		$V_{DM} = 536\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$; exponential waveform; gate open circuit	2000	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$; $I_{T(\text{RMS})} = 8\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; gate open circuit; snubberless condition	12	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common	 <p style="text-align: center;">D2PAK (SOT404A)</p>	 <p style="text-align: center;">003aaf296</p>
2	LD	load		
3	G	gate		
mb	LD	mounting base; load		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
ACTT8B-800CTN	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404A

7. Marking

Table 4. Marking codes

Type number	Marking code
ACTT8B-800CTN	ACTT8B-800CTN

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 131\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	80	A
		full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 16.7\text{ ms}$	-	88	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	32	A^2s
dl_T/dt	rate of rise of on-state current	$I_G = 70\text{ mA}$	-	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current	$t = 20\text{ }\mu\text{s}$	-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$
V_{PP}	peak pulse voltage	$T_j = 25\text{ }^{\circ}\text{C}$; non-repetitive, off-state; Fig. 6	-	2	kV

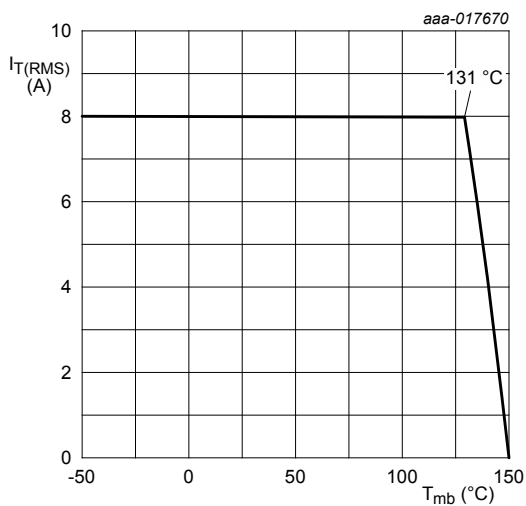
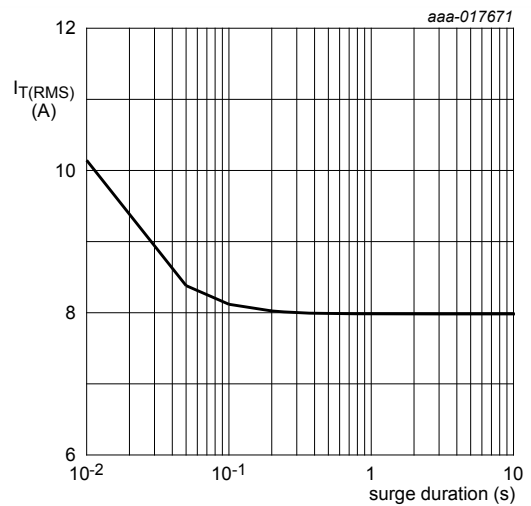


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50\text{ Hz}$; $T_{mb} = 131\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

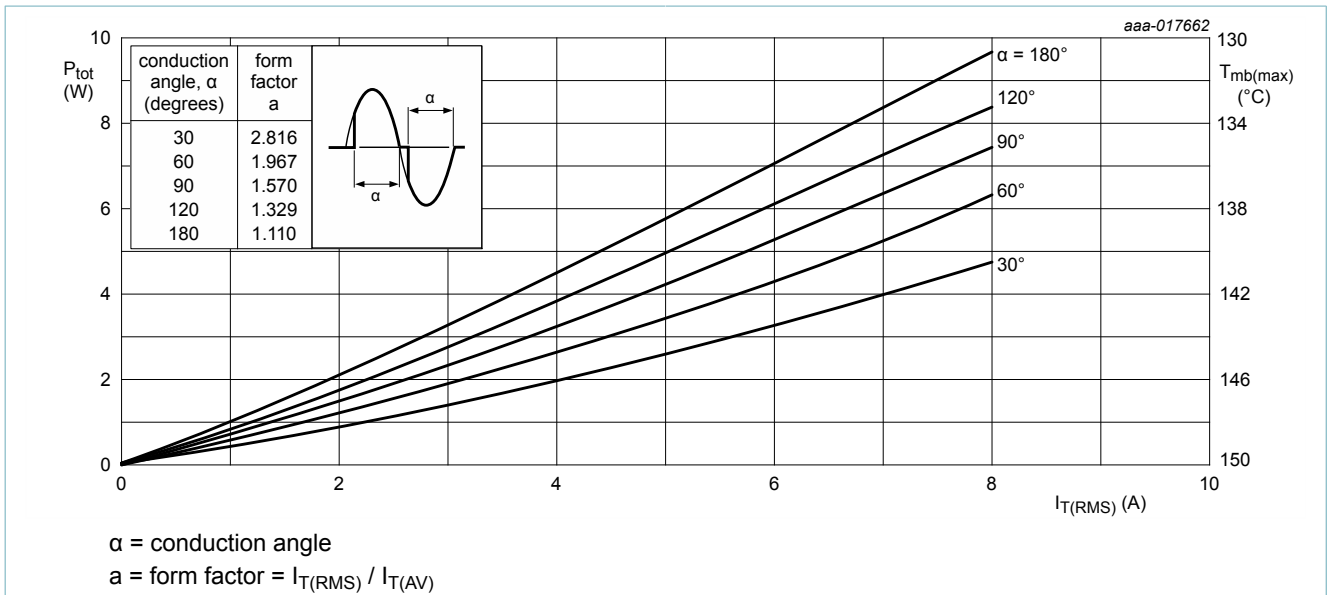


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

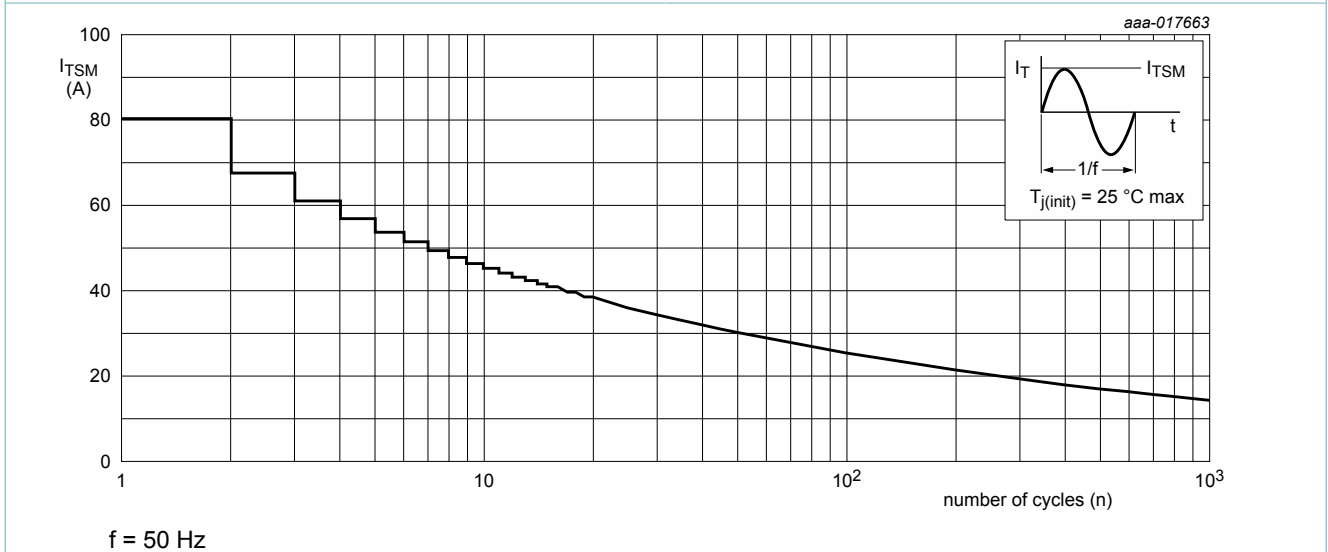


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

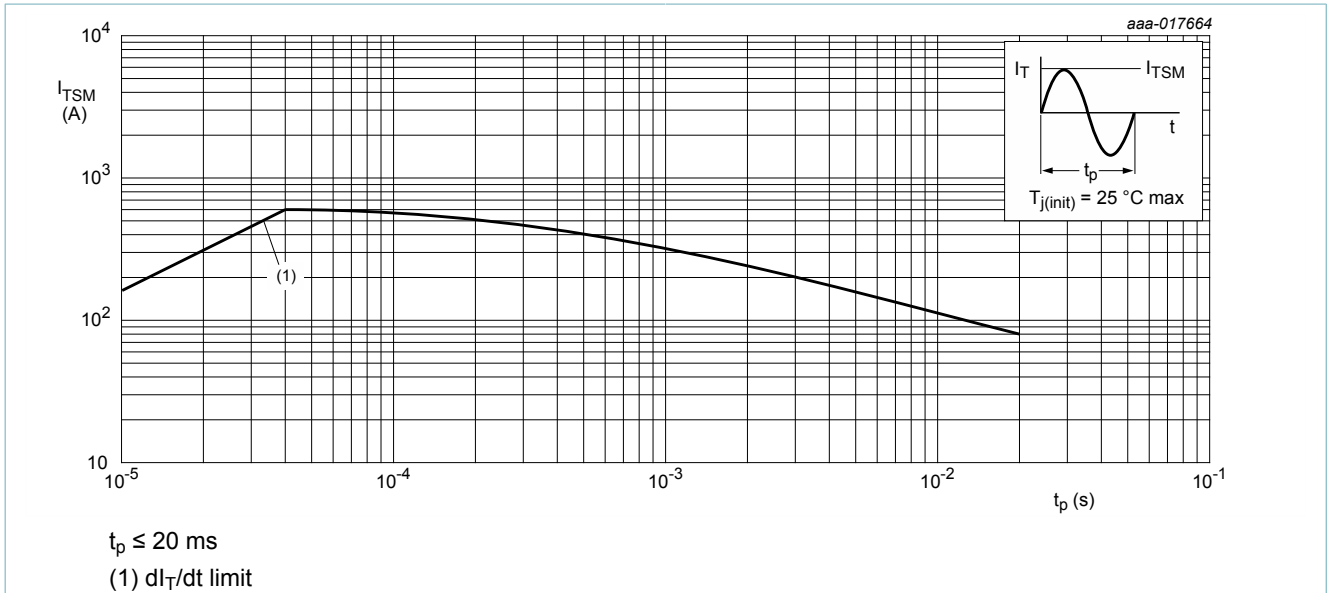


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

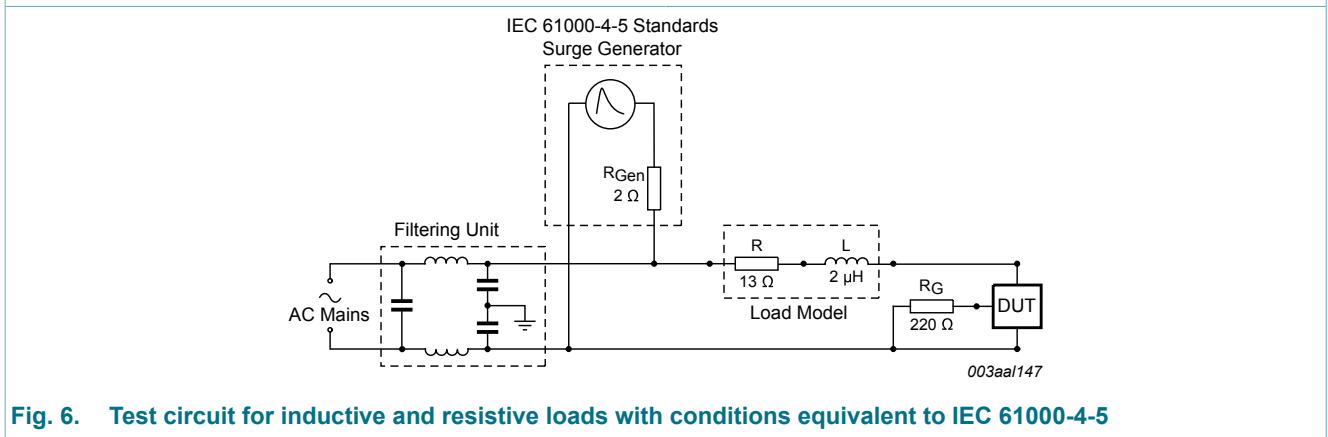


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig. 7	-	-	2	K/W
		half cycle	-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; printed circuit board (FR4) mounted	-	55	-	K/W

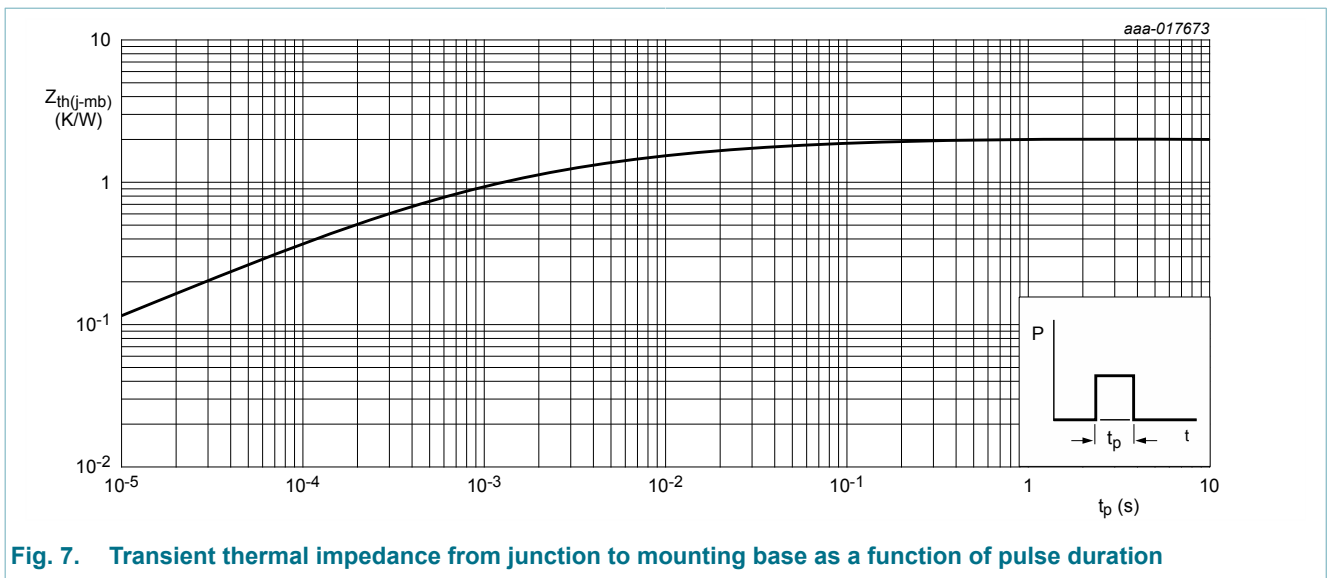


Fig. 7. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 100 mA; LD+ G+; T _j = 25 °C; Fig. 8	5	-	35	mA
		V _D = 12 V; I _T = 100 mA; LD+ G-; T _j = 25 °C; Fig. 8	5	-	35	mA
		V _D = 12 V; I _T = 100 mA; LD- G-; T _j = 25 °C; Fig. 8	5	-	35	mA
I _L	latching current	V _D = 12 V; I _G = 100 mA; LD+ G+; T _j = 25 °C; Fig. 9	-	-	50	mA
		V _D = 12 V; I _G = 100 mA; LD+ G-; T _j = 25 °C; Fig. 9	-	-	60	mA
		V _D = 12 V; I _G = 100 mA; LD- G-; T _j = 25 °C; Fig. 9	-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 10	-	-	40	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; Fig. 11	-	-	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 100 mA; T _j = 25 °C; Fig. 12	-	0.8	1	V
		V _D = 400 V; I _T = 100 mA; T _j = 150 °C; Fig. 12	0.2	0.45	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C	-	-	10	µA
		V _D = 800 V; T _j = 150 °C	-	-	2	mA
V _{CL}	clamping voltage	I _{CL} = 0.1 mA; t _p = 1 ms; T _j = 25 °C	850	-	-	V
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	4000	-	-	V/µs
		V _{DM} = 536 V; T _j = 150 °C; exponential waveform; gate open circuit	2000	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 8 A; dV _{com} /dt = 20 V/µs; gate open circuit; snubberless condition	12	-	-	A/ms
		V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 8 A; dV _{com} /dt = 10 V/µs; gate open circuit	15	-	-	A/ms
		V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 8 A; dV _{com} /dt = 1 V/µs; gate open circuit	20	-	-	A/ms

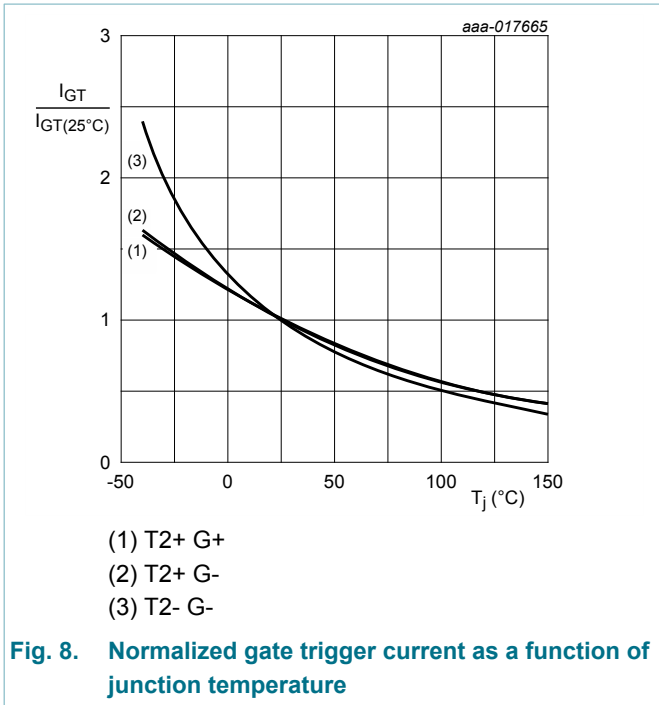


Fig. 8. Normalized gate trigger current as a function of junction temperature

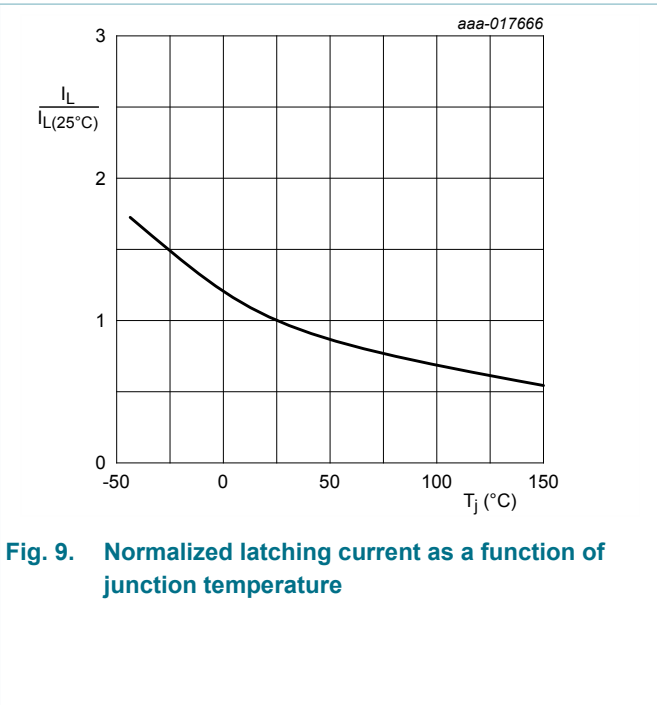


Fig. 9. Normalized latching current as a function of junction temperature

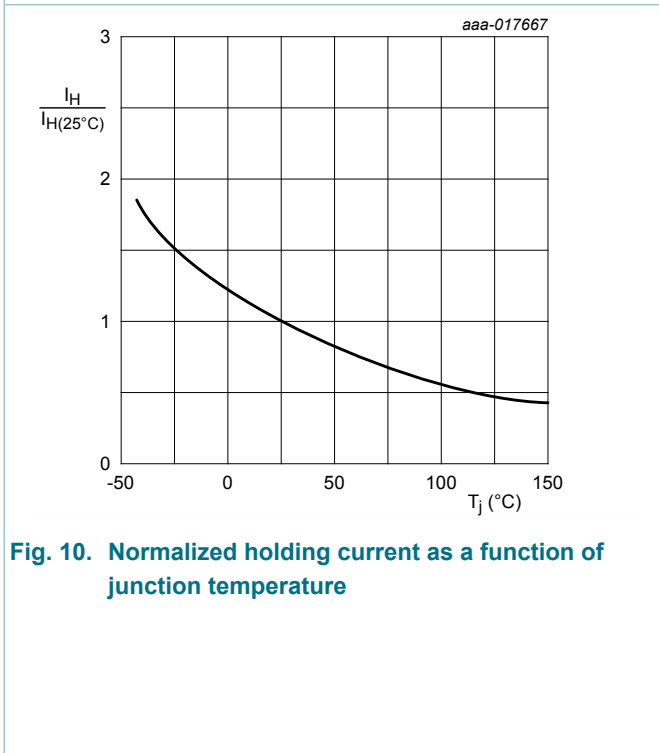


Fig. 10. Normalized holding current as a function of junction temperature

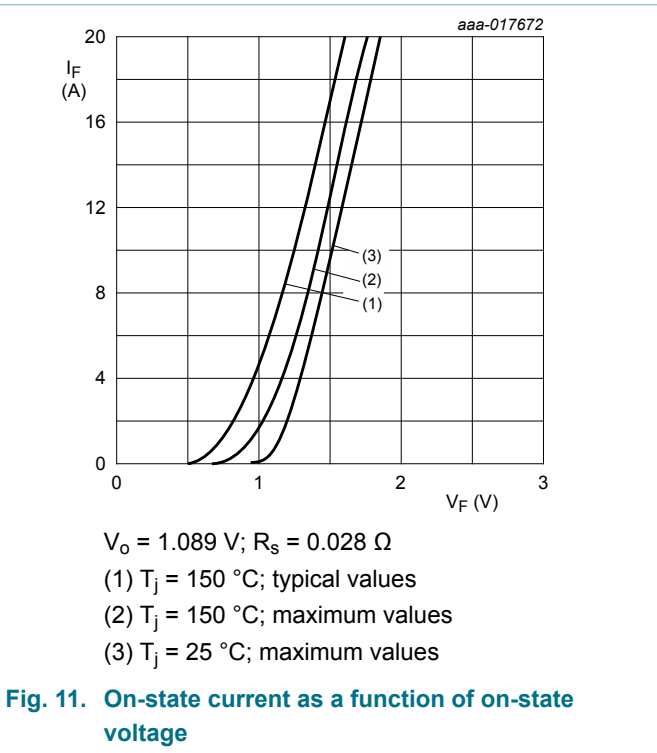
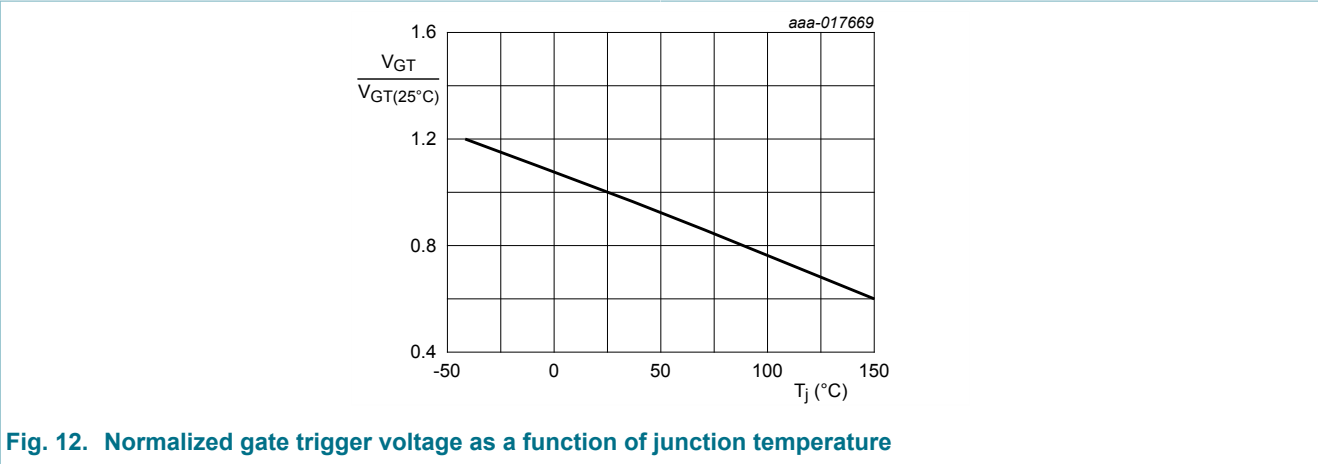
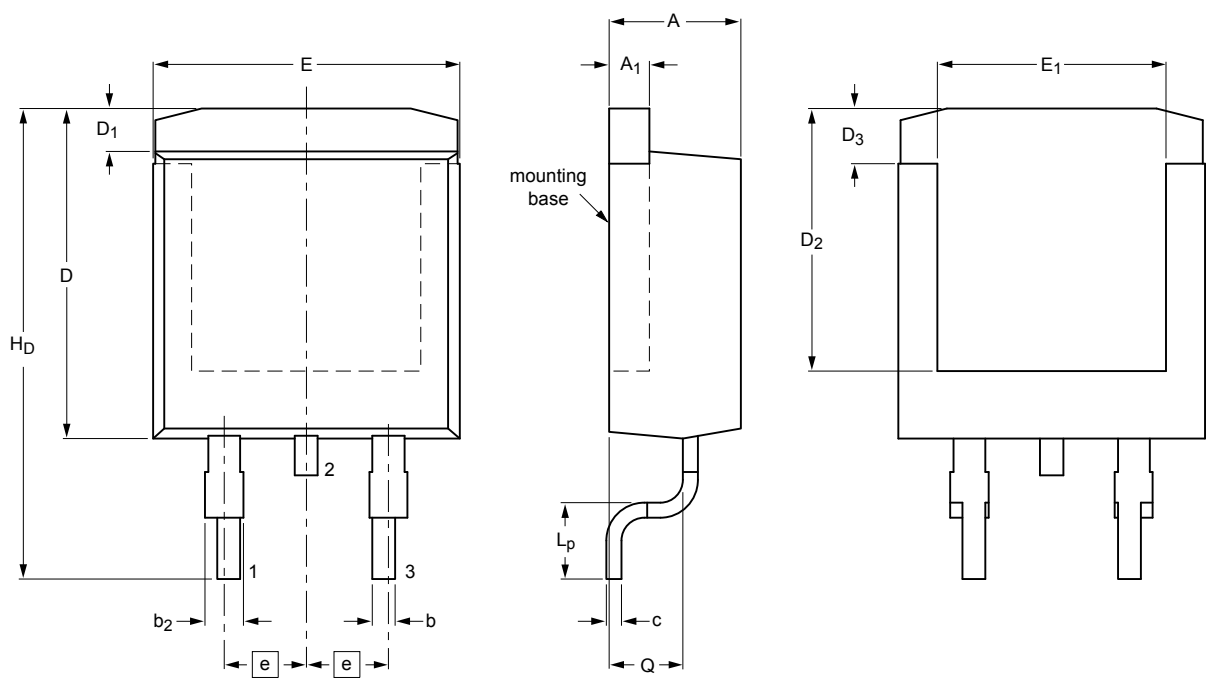


Fig. 11. On-state current as a function of on-state voltage



11. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) SOT404A



Dimensions (mm are the original dimensions)

Unit	A	A ₁	b	b ₂	c	D _{max}	D ₁	D ₂	D ₃	E	E ₁	e	H _D	L _p	Q
max	4.5	1.40	0.85	1.45	0.64	11	1.6	8.6	1.85	10.3	8.1		15.8	2.9	2.6
nom												2.54			
min	4.1	1.27	0.60	1.05	0.46		1.2	8.0	1.40	9.7	7.6		14.8	2.1	2.2

sot404a_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT404A						13-02-28 13-03-12

Fig. 13. Package outline D2PAK (SOT404A)

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	3
7	Marking	3
8	Limiting values	4
9	Thermal characteristics	7
10	Characteristics	8
11	Package outline	11
12	Legal information	12
12.1	Data sheet status	12
12.2	Definitions	12
12.3	Disclaimers	12
12.4	Trademarks	13

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